

Silicon NPN Power Transistors

2SB1037

DESCRIPTION

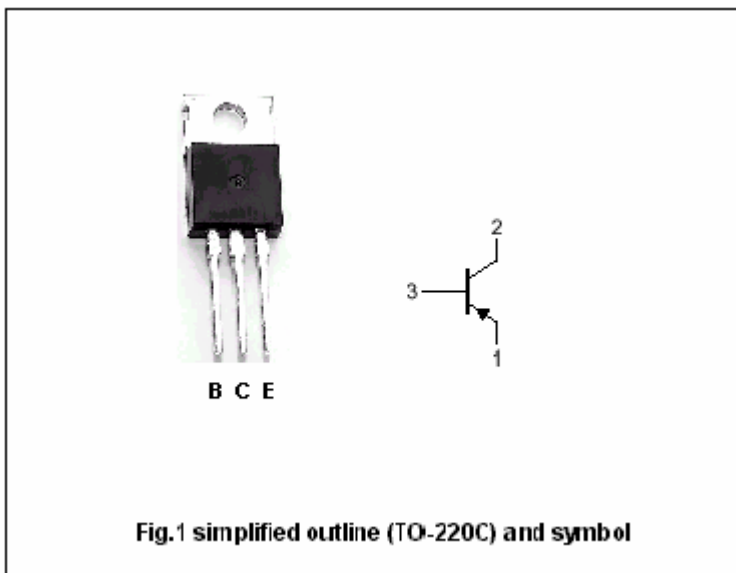
- With TO-220 package
- High allowable collector dissipation.
- Complement to type 2SD1459

APPLICATIONS

- For color TV vertical output, sound output applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings (Ta=25 )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-150	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-150	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-1.5	A
I <sub>CM</sub>	Collector current-peak		-3	A
P <sub>C</sub>	Collector power dissipation		2.0	W
		T <sub>C</sub> =25	30	
T <sub>j</sub>	Junction temperature		175	
T <sub>stg</sub>	Storage temperature		-55~175	

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## CHARACTERISTICS

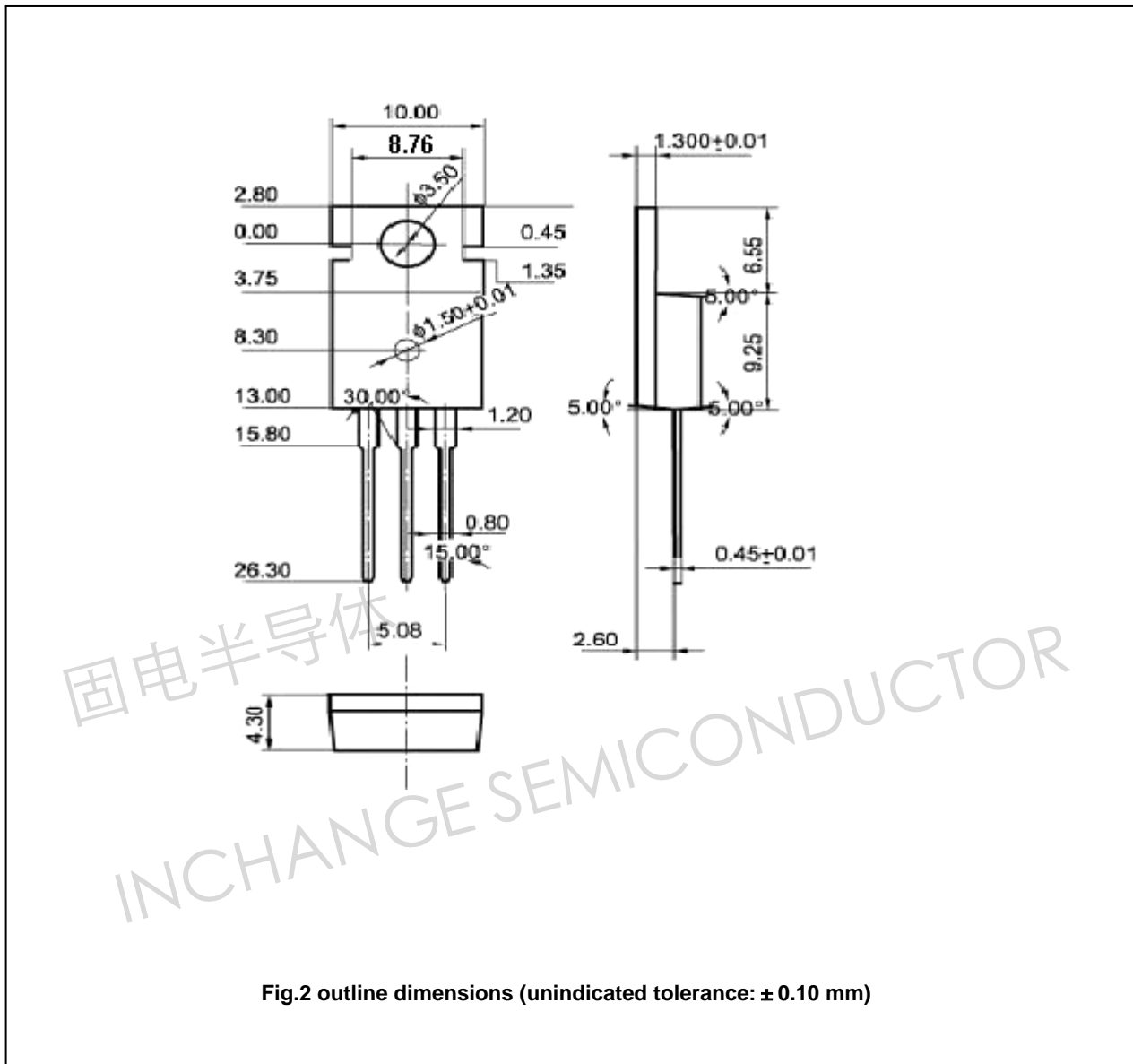
T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-10mA ; I <sub>B</sub> =0	-150			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-0.5A, I <sub>B</sub> =-50mA			-1.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-0.5A, I <sub>B</sub> =-50mA			-1.2	V
I <sub>CBO</sub>	Collector cut-offcurrent	V <sub>CB</sub> =-120V; I <sub>E</sub> =0			-10	μA
I <sub>EBO</sub>	Emitter cut-offcurrent	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-10	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-0.3A ; V <sub>CE</sub> =-5V	70		200	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.1A ; V <sub>CE</sub> =-5V		15		MHz

◆ h<sub>FE</sub> classifications

Q	R
70-140	100-200

PACKAGE OUTLINE



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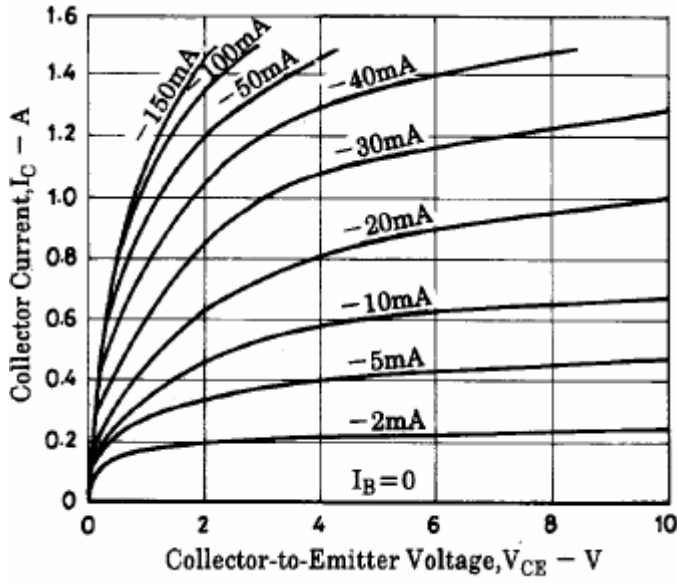


Fig.3 Static Characteristic

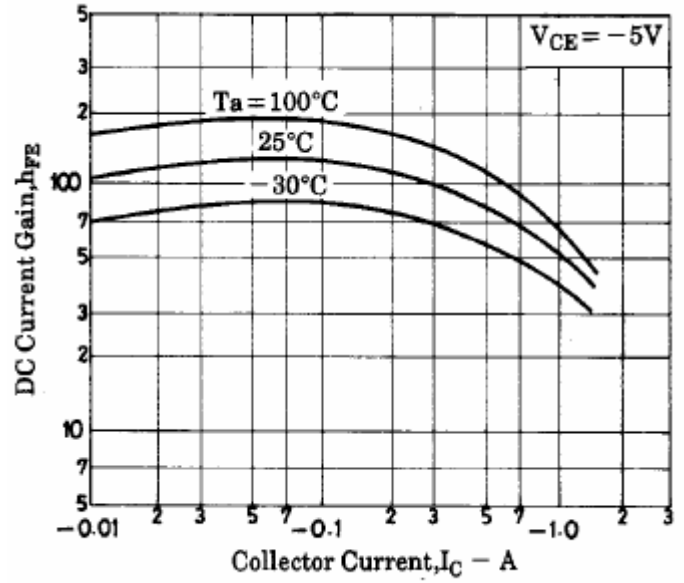


Fig.4 DC current Gain

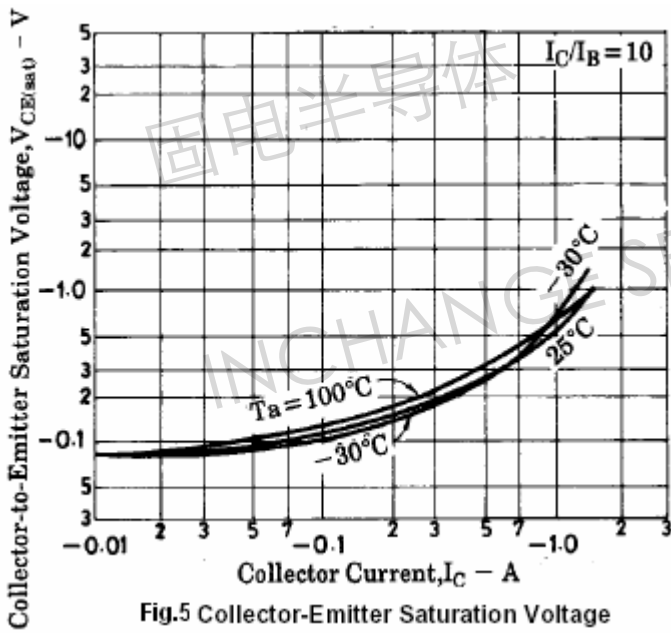


Fig.5 Collector-Emmitter Saturation Voltage

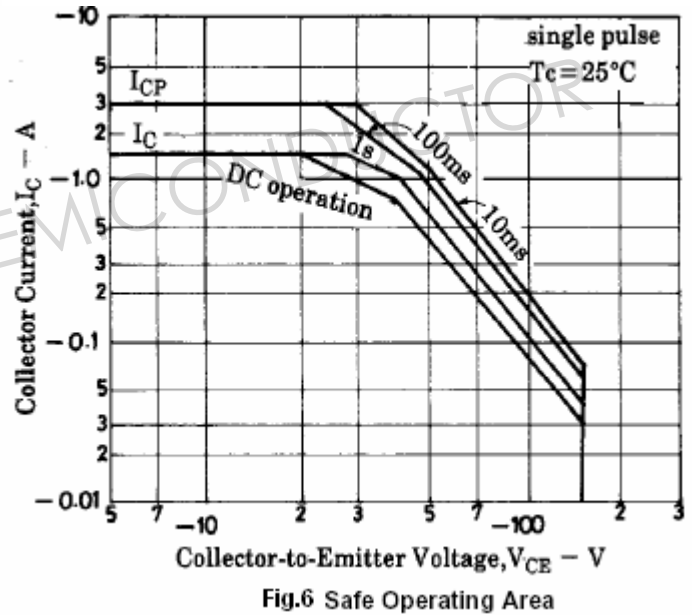


Fig.6 Safe Operating Area